

L850F-36U

Infrared LED Lamp

L850F-36U is lower forward voltage and higher output power LED. It consists an AlGaAs LED 400 micron square and mounted on a lead frame with a clear epoxy lens. On forward bias it emits a spectral band of radiation, which peaks at 850nm. These devices are intended to be operated at pulsed current of 1A under typical 3.5V for stable long life.

<Specifications>

1. Product Name: Infrared LED Lamp

2. Type Number: L850F-36U

3. Chip:

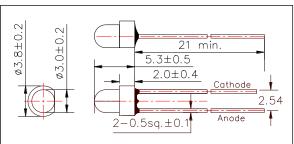
Chip material: AlGaAsDimension: 400um x 400um

- Peak Wavelength: 850nm typ.

4.Package

Type: Φ3mm Clear Molding
Resin Material: Epoxy Resin
Lead Frame: Soldered

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]							
Item	Symbol	Maximum Rated Value	Unit				
Power Dissipation	PD	150	mW				
Forward Current	IF	100	mA				
Pulse Forward Current*	IFP	1000	mA				
Reverse Voltage	VR	5	V				
Operating Temperature	TOPR	-30 ~ +85	°C				
Storage Temperature	TSTG	-30 ~ +100	°C				
Soldering Temperature**	TSOL	260	°C				

^{*} Duty=1% and Pulse Width=10us.

^{**} Soldering condition must be completed within 3 second at 260 °C.

Electro-Optical Characteristics [Ta=25℃]								
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit		
Forward Voltage	VF	IF=50mA		1.45	1.50	V		
Pulsed Forward Voltage	VFP	IFP=1A		3.5	4.0			
Reverse Current	IR	VR=5V			10	uA		
Total Radiated Power*	PO	IF=50mA	18	24		mW		
Radiant Intensity**	IE	IF=50mA		35		mW/sr		
Peak wavelength	λР	IF=50mA	840	850	860	nm		
Half Width	Δλ	IF=50mA		40		nm		
Viewing Half Angle	θ1/2	IF=50mA		±30		deg		
Rise Time	tr	IF=50mA		15		ns		
Fall Time	tf	IF=50mA		10		ns		

^{*} Measured by Photodyne #500



^{**} Measured by Tektronix J-6512